



## 30V N-Channel Enhancement Mode MOSFET

Voltage

30 V

Current

10 A

#### **Features**

- R<sub>DS(ON)</sub>, V<sub>GS</sub>@10V, I<sub>D</sub>@10A<11.5mΩ
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_{D}@6A<15m\Omega$
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

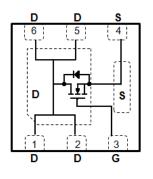
• Case: DFN2020B-6L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0003 ounces, 0.0086 grams

# DFN2020B-6L





## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

| PARAMETER   |                      | SYMBOL                           | LIMIT       | UNITS |  |
|---|----------------------|----------------------------------|-------------|-------|--|
| Drain-Source Voltage  |                      | V <sub>DS</sub>                  | 30          | V     |  |
| Gate-Source Voltage   |                      | V <sub>G</sub> s                 | <u>+</u> 20 |       |  |
| Continuous Drain Current (Note 4)                           |                      | I <sub>D</sub>                   | 10          | A     |  |
| Pulsed Drain Current (Note 1)                               |                      | I <sub>DM</sub>                  | 40          |       |  |
| Power Dissipation   | T <sub>A</sub> =25°C | P <sub>D</sub>                   | 2           | W     |  |
|   | Derate above 25°C    |                                  | 16          | mW/°C |  |
| Operating Junction and Storage Temperature Range            |                      | T <sub>J</sub> ,T <sub>STG</sub> | -55~150     | °C    |  |
| Typical Thermal Resistance - Junction to Ambient (Note 4,5) |                      | Reja                             | 62.5        | °C/W  |  |





## **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

| PARAMETER                        | SYMBOL              | TEST CONDITION   | MIN. | TYP. | MAX.         | UNITS |  |  |
|----------------------------------|---------------------|--|------|------|--------------|-------|--|--|
| Static                           |                     |  |      |      |              |       |  |  |
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =250uA                                     | 30   | -    | -            | \ \   |  |  |
| Gate Threshold Voltage           | $V_{GS(th)}$        | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA                       | 1    | 1.7  | 2.5          | V     |  |  |
|                                  | _                   | V <sub>GS</sub> =10V, I <sub>D</sub> =10A                                      | -    | 7.5  | 11.5         |       |  |  |
| Drain-Source On-State Resistance | R <sub>DS(on)</sub> | V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A                                      | -    | 11   | 15           | mΩ    |  |  |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>    | V <sub>DS</sub> =30V, V <sub>GS</sub> =0V                                      | -    | -    | 1            | uA    |  |  |
| Gate-Source Leakage Current      | Igss                | V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V                            | -    | -    | <u>+</u> 100 | nA    |  |  |
| Dynamic (Note 6)                 |                     |  |      |      |              |       |  |  |
| Total Gate Charge                | $Q_g$               | V <sub>DS</sub> =15V, I <sub>D</sub> =10A,<br>V <sub>GS</sub> =4.5V (Note 2,3) | -    | 6.9  | -            | nC    |  |  |
| Gate-Source Charge               | $Q_gs$              |  | -    | 2.7  | -            |       |  |  |
| Gate-Drain Charge                | $Q_gd$              |  | -    | 1.8  | -            |       |  |  |
| Input Capacitance                | Ciss                | V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,<br>f=1MHZ                           | -    | 781  | -            | pF    |  |  |
| Output Capacitance               | Coss                |  | -    | 158  | -            |       |  |  |
| Reverse Transfer Capacitance     | Crss                |  | -    | 92   | -            |       |  |  |
| Turn-On Delay Time               | td <sub>(on)</sub>  | $V_{DS}{=}15V,\ I_{D}{=}10A,$ $V_{GS}{=}10V,\ R_{G}{=}6\Omega$ (Note 2,3)      | -    | 5.4  | -            |       |  |  |
| Turn-On Rise Time                | tr                  |  | -    | 86   | -            | ns    |  |  |
| Turn-Off Delay Time              | td <sub>(off)</sub> |  | -    | 20   | -            |       |  |  |
| Turn-Off Fall Time               | tf                  |  | -    | 10   | -            |       |  |  |
| Drain-Source Diode               |                     |  |      |      |              |       |  |  |
| Maximum Continuous Drain-Source  | ,                   |  |      |      | 1.5          | А     |  |  |
| Diode Forward Current            | I <sub>S</sub>      |  | -    |      |              |       |  |  |
| Diode Forward Voltage            | $V_{SD}$            | I <sub>S</sub> =1A, V <sub>GS</sub> =0V  | -    | 0.73 | 1            | V     |  |  |

#### NOTES:

- 1. Pulse width<a>300us</a>, Duty cycle<a>2%</a>.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

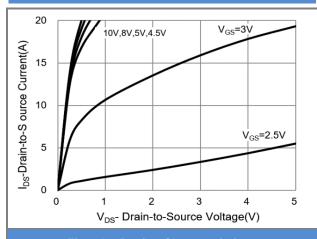


Fig.1 On-Region Characteristics

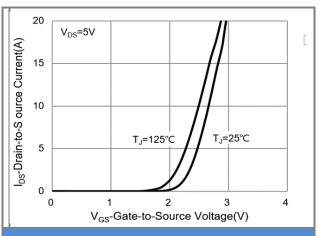


Fig.2 Transfer Characteristics

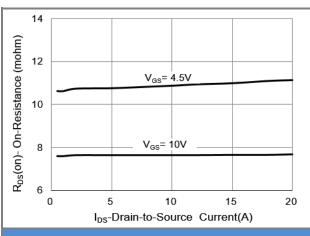


Fig.3 On-Resistance vs. Drain Current

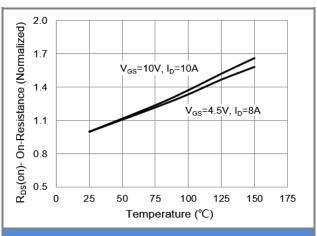
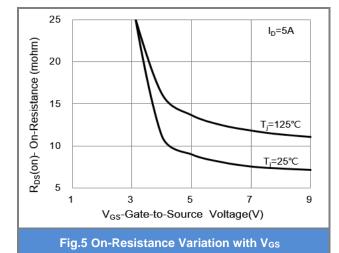
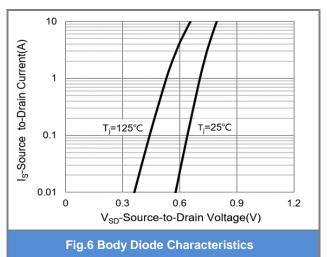


Fig.4 On-Resistance vs. Junction temperature









#### **TYPICAL CHARACTERISTIC CURVES**

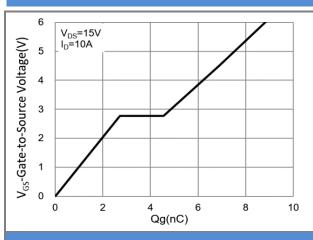


Fig.7 Gate-Charge Characteristics

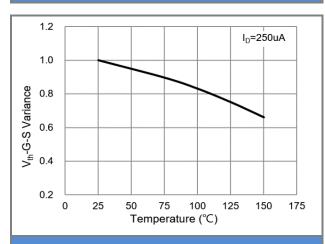


Fig.9 Threshold Voltage Variation with Temperature

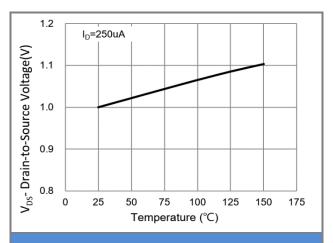


Fig.8 Breakdown Voltage Variation vs. Temperature

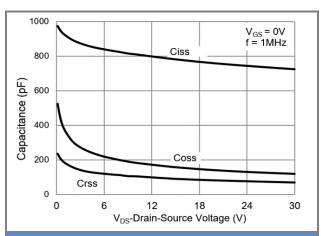


Fig.10 Capacitance vs. Drain-Source Voltage

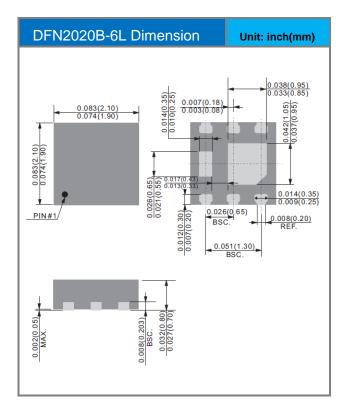


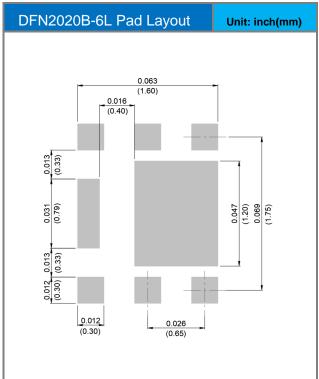


## Part No. Packing Code Version

| Part No. Packing Code | Package Type | Packing Type     | Marking | Version                        |
|-----------------------|--------------|------------------|---------|--------------------------------|
| PJQ2408_R1_00001      | DFN2020B-6L  | 3K pcs / 7" reel | 408     | Halogen free<br>RoHS compliant |

## **Packaging Information & Mounting Pad Layout**









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